Notice of Allowability	Application No.	Applicant(s)
	09/633,002	ISHIBASHI, KEIJI
	Examiner	Art Unit
	Wesley D. Markham	1762
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI	(OR REMAINS) CLOSED in this ap or other appropriate communicatior GHTS. This application is subject to	plication. If not included now will be mailed in due course. THIS
1. $\boxtimes$ This communication is responsive to <u>the after-final amendance</u>	ment dated 3/31/2005.	
2. The allowed claim(s) is/are <u>27-32</u> .	·	
3. $\boxtimes$ The drawings filed on <u>04 August 2000</u> are accepted by the	Examiner.	
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority un a)  All b)  Some* c)  None of the: <ol> <li>Certified copies of the priority documents have</li> <li>Certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have</li> <li>Copies of the certified copies of the priority documents have</li> <li>The priority docum</li></ol></li></ul>	been received. been received in Application No cuments have been received in this of this communication to file a reply	national stage application from the
A SUBSTITUTE OATH OR DECLARATION must be submi     INFORMAL PATENT APPLICATION (PTO-152) which give		
<ul> <li>6. ☐ CORRECTED DRAWINGS (as "replacement sheets") muss</li> <li>(a) ☐ including changes required by the Notice of Draftspers</li> <li>1) ☐ hereto or 2) ☐ to Paper No./Mail Date</li> <li>(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date</li> </ul>	t be submitted. on's Patent Drawing Review(PTO-	.948) attached
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the		
<ol> <li>DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT F</li> </ol>	sit of BIOLOGICAL MATERIAL r	nust be submitted. Note the
Attachment(s)  1. Notice of References Cited (PTO-892)  2. Notice of Draftperson's Patent Drawing Review (PTO-948)  3. Information Disclosure Statements (PTO-1449 or PTO/SB/06 Paper No./Mail Date	6. ☐ Interview Summary Paper No./Mail Dat 8), 7. ☐ Examiner's Amendr	te
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**Notice of Allowability** 

## **DETAILED ACTION / ALLOWANCE**

# Response to Amendment

Acknowledgement is made of the after-final amendment filed by the applicant on 3/31/2005 (with a certificate of mailing dated 3/28/2005), in which the applicant proposed to cancel Claims 11 – 16 and 33. This amendment has been entered.
 Claims 27 – 32 are currently pending in U.S. Application Serial No. 09/633,002, and an Office Action on the merits follows.

# **Drawings**

2. The formal drawings (2 sheets, 3 figures) filed on 8/4/2000 are approved by the examiner.

### Allowable Subject Matter

- 3. Claims 27 32 are allowed.
- 4. The following is an examiner's statement of reasons for allowance: Independent Claim 27, from which Claims 28 32 depend, requires <u>removing a deposited film</u> from a wall inside a chamber by heating a <u>platinum</u>-containing hot element, the hot element disposed away from the wall and the deposited film, to a temperature of 400° C or higher without generating a <u>plasma</u>, supplying the chamber with a cleaning gas containing at least one of <u>a fluorine atom and a chlorine atom</u> and first contacting the hot element with the gas to activate the gas, thereafter contacting the deposited film with the activated cleaning gas and converting the film into a gaseous

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substance, and removing the gaseous substance from the chamber. A summary of the closest prior art of record follows. Yamanaka et al. (USPN 6,592,771) teaches a method for etching a film on a substrate located in a vacuum apparatus, the vacuum apparatus having a chamber, the method comprising providing a hot element "46" in the chamber, the hot element disposed away from the deposited film and having at least a surface which comprises platinum, placing the substrate in the chamber. exhausting the chamber, heating the hot element to 400° C or higher, supplying into the chamber a cleaning gas containing at least one of a fluorine atom and a chlorine atom, contacting the cleaning gas with the heated hot element to decompose and/or activate the cleaning gas and generate an activated species therefrom, and allowing the activated species to etch the deposited film on the substrate. Muranaka et al. (USPN 6,410,454) similarly teaches removing contaminants on the surface of a semiconductor wafer by activating a halogen-containing gas with a heated filament made of platinum and then contacting the activated cleaning gas with the surface of the wafer. However, both of the above cited references are drawn to etching / cleaning a substrate, not removing a deposited film from a wall inside a chamber, as required by the applicant's claims. In fact, the chamber wall cleaning process taught by Yamanaka et al. uses a fluorine-based gas plasma, not hot element activation without the generation of a plasma as required by the claims. As such, neither reference, alone or in any reasonable combination, teaches or suggests performing the applicant's claimed method. Bluck et al. (USPN 6,101,972) teaches a method for removing a deposited film from a wall inside a chamber, the method comprising

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providing a "hot element" (i.e., filaments "32" and "42") in the chamber, the hot element disposed away from the wall of the chamber and the deposited film, exhausting the chamber, heating the hot element, supplying a cleaning gas into the chamber and first contacting the hot element with the gas to thereby activate the gas, and contacting the deposited film with the activated cleaning gas to clean the walls of the chamber. However, Bluck et al. does not teach that the filaments are composed of platinum, as required by the claims. Additionally, Bluck et al. clearly teaches and desires forming a plasma while heating the hot element in the chamber in order to perform the CVD and chamber cleaning processes (see the entire Bluck et al. reference, including the title). Therefore, Bluck et al., alone or in combination, does not teach or reasonably suggest heating the hot element without generating a plasma in the context of the applicant's claims. For the above reasons, the prior art of record, alone or in combination, does not teach or reasonably suggest each and every limitation of independent Claim 27, and this claim is allowed. Claims 28 – 32 depend from Claim 27 and are therefore also allowed.

5. As set forth in paragraph 13 of the previous Office Action (i.e., the final Office Action mailed on 12/30/2004), the examiner again notes that, in allowing Claims 27 – 32, the "wall inside a chamber" from which the deposited film is removed, as required by the claims, has been interpreted to be any of the inside walls of the chamber (see, for example, page 8, lines 28 – 30, and page 9, lines 16 – 19, of the specification, which support the examiner's interpretation of the claims). Therefore, etching / removing a deposited film from the "walls" of a substrate inside the chamber (e.g.,

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the walls of a trench in a semiconductor substrate or device) would not be encompassed by the applicant's claims.

6. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Wesley D. Markham whose telephone number is (571) 272-1422. The examiner can normally be reached on Monday - Friday, 8:00 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tim Meeks can be reached on (571) 272-1423. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Wesley D Markham Examiner

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TIMOTHY MEEKS
SUPERVISORY PATENT EXAMINER